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## The Formation of InAs Quantum Dots in an Aluminum Oxide Matrix

[D. A. Tenne](#),<sup>1</sup> [O. R. Bajutova](#),<sup>1</sup> [A. K. Bakarov](#),<sup>1</sup> [A. K. Kalagin](#),<sup>1</sup> [A. G. Milekhin](#),<sup>1</sup> [A. I. Toropov](#),<sup>1</sup> and [D. R. T. Zahn](#)<sup>2</sup>

<sup>1</sup>*Institute of Semiconductor Physics, Siberian Division, Russian Academy of Sciences, Novosibirsk, 630090 Russia*

<sup>2</sup>*Institut für Physik, Universität Chemnitz, D-09107 Chemnitz, Germany*

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The formation of InAs quantum dots in an aluminum oxide matrix by selective oxidation of AlAs layers in an InAs/AlAs heterostructure is studied. According to the Raman spectroscopy data, the process of selective oxidation leads to stress relaxation in the InAs quantum dots and to the formation of amorphous arsenic at the boundary between oxidized and unoxidized regions. ©2002 MAIK "Nauka / Interperiodica".

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